

# C2D10120A Silicon Carbide Schottky Diode

# ZERO RECOVERY® RECTIFIER

 $\mathbf{V}_{\mathsf{RRM}}$ 1200 V  $I_{r}(T_{c}=135^{\circ}C) = 14.5 A$ Q 61 nC

#### **Features**

- 1.2kV Schottky Rectifier
- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Extremely Fast Switching
- Positive Temperature Coefficient on V<sub>F</sub>

## **Benefits**

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

# PIN 2O-

**Package** 

TO-220-2

# **Applications**

- Switch Mode Power Supplies
- **Power Factor Correction**
- **Motor Drives**



Part Number	Package	Marking
C2D10120A	TO-220-2	C2D10120

Halogen-Free

## Maximum Ratings (T<sub>c</sub>=25°C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V <sub>RRM</sub>	Repetitive Peak Reverse Voltage	1200	V		
V <sub>RSM</sub>	Surge Peak Reverse Voltage	1200	V		
V <sub>DC</sub>	DC Blocking Voltage	1200	V		
I <sub>F</sub>	Continuous Forward Current	31 14.5 10	А	T <sub>c</sub> =25°C T <sub>c</sub> =135°C T <sub>c</sub> =152°C	
$I_{\sf FRM}$	Repetitive Peak Forward Surge Current	50	А	$T_c$ =25°C, $t_p$ =10 ms, Half Sine Wave	
$I_{FSM}$	Non-Repetitive Peak Forward Surge Current	250	А	T <sub>c</sub> =25°C, t <sub>p</sub> =10 μs, Pulse	
P <sub>tot</sub>	Power Dissipation	312 135	W	T <sub>c</sub> =25°C T <sub>c</sub> =110°C	
$T_{J}$ , $T_{stg}$	Operating Junction and Storage Temperature	-55 to +175	°C		
	TO-220 Mounting Torque	1 8.8	Nm lbf-in	M3 Screw 6-32 Screw	



### **Electrical Characteristics**

Symbol	Parameter	Тур.	Max.	Unit	Test Conditions	Note
V <sub>F</sub>	Forward Voltage	1.6 2.5	1.8 3.0	V	$I_F = 10 \text{ A } T_J = 25 ^{\circ}\text{C}$ $I_F = 10 \text{ A } T_J = 175 ^{\circ}\text{C}$	
$I_{_{R}}$	Reverse Current	10 20	200 1000	μΑ	$V_R = 1200 \text{ V } T_J = 25 ^{\circ}\text{C}$ $V_R = 1200 \text{ V } T_J = 150 ^{\circ}\text{C}$	
Q <sub>c</sub>	Total Capacitive Charge	61		nC	$V_R = 1200 \text{ V, } I_F = 10 \text{ A}$ $di/dt = 500 \text{ A/}\mu\text{s}$ $T_J = 25^{\circ}\text{C}$	
С	Total Capacitance	1000 80 59		pF	$V_R = 0 \text{ V, } T_J = 25^{\circ}\text{C, } f = 1 \text{ MHz}$ $V_R = 200 \text{ V, } T_J = 25^{\circ}\text{C, } f = 1 \text{ MHz}$ $V_R = 400 \text{ V, } T_J = 25^{\circ}\text{C, } f = 1 \text{ MHz}$	

#### Note:

### **Thermal Characteristics**

Symbol	Parameter	Тур.	Unit
$R_{\theta JC}$	Thermal Resistance from Junction to Case	0.48	°C/W

# **Typical Performance**

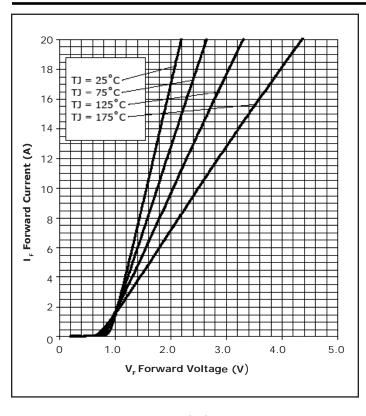


Figure 1. Forward Characteristics

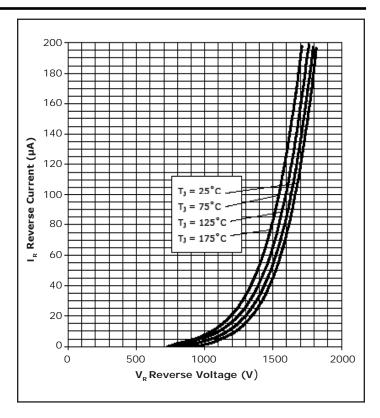
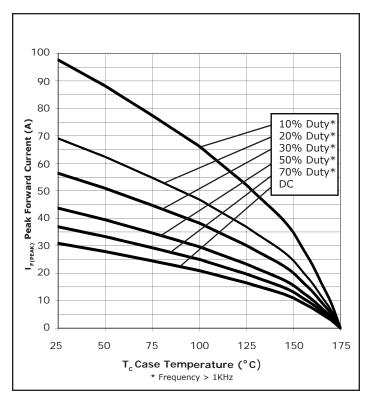


Figure 2. Reverse Characteristics

<sup>1.</sup> This is a majority carrier diode, so there is no reverse recovery charge.



## **Typical Performance**



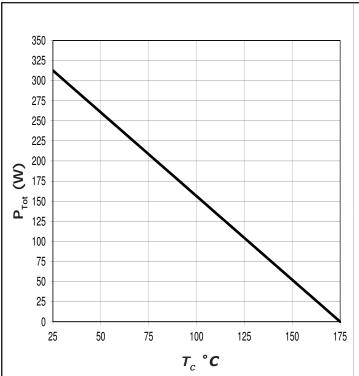


Figure 3. Current Derating

Figure 4. Power Derating

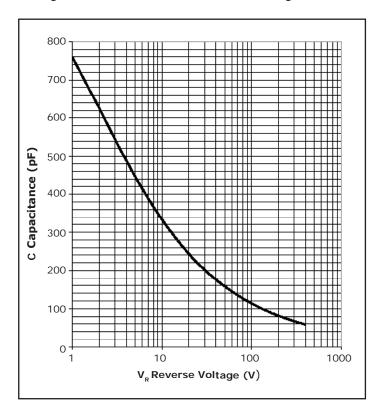


Figure 5. Capacitance vs. Reverse Voltage



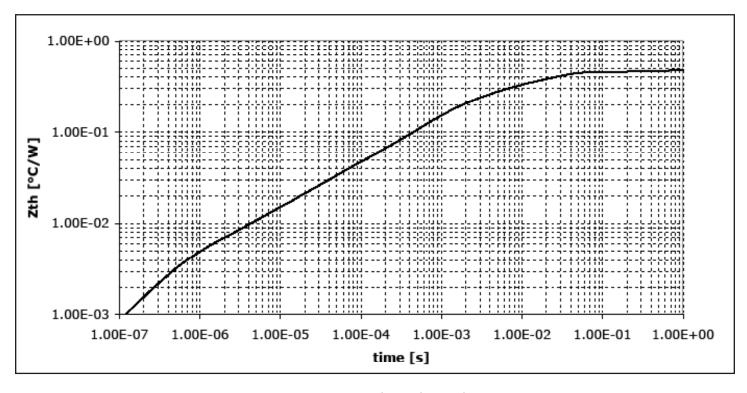


Figure 6. Transient Thermal Impedance

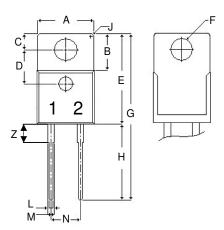


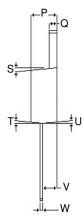
## **Package Dimensions**

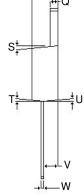
Package TO-220-2

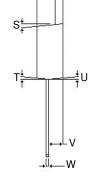
PIN 1O-

PIN 20-











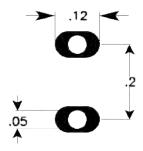
	POS	Inc	hes	Millimeters		
	PUS	Min	Max	Min	Max	
	А	.381	.410	9.677	10.414	
	В	.235	.255	5.969	6.477	
	С	.100	.120	2.540	3.048	
	D	.223	.337	5.664	8.560	
	E	.590	.615	14.986	15.621	
	F	.143	.153	3.632	3.886	
١	G	1.105	1.147	28.067	29.134	
	Н	.500	.550	12.700	13.970	
	L	.025	.036	.635	.914	
	М	.045	.055	1.143	1.397	
	N	.195	.205	4.953	5.207	
	Р	.165	.185	4.191	4.699	
	Q	.048	.054	1.219	1.372	
	S	3°	6°	3°	6°	
	Т	3°	6°	3°	6°	
	U	3°	6°	3°	6°	
	V	.094	.110	2.388	2.794	
	W	.014	.025	.356	.635	
	Х	3°	5.5°	3°	5.5°	
	Υ	.385	.410	9.779	10.414	
	z	.130	.150	3.302	3.810	

#### NOTE:

1. Dimension L, M, W apply for Solder Dip

# **Recommended Solder Pad Layout**

O CASE



TO-220-2

Part Number	Package	Marking
C2D10120A	TO-220-2	C2D10120

Note: Recommended soldering profiles can be found in the applications note here: http://www.cree.com/power\_app\_notes/soldering





#### **Notes**

#### RoHS Compliance

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS2), as implemented January 2, 2013. RoHS Declarations for this product can be obtained from your Cree representative or from the Product Documentation sections of www.cree.com.

#### • REACh Compliance

REACh substances of high concern (SVHCs) information is available for this product. Since the European Chemical Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact a Cree representative to insure you get the most up-to-date REACh SVHC Declaration. REACh banned substance information (REACh Article 67) is also available upon request.

• This product has not been designed or tested for use in, and is not intended for use in, applications implanted into the human body nor in applications in which failure of the product could lead to death, personal injury or property damage, including but not limited to equipment used in the operation of nuclear facilities, life-support machines, cardiac defibrillators or similar emergency medical equipment, aircraft navigation or communication or control systems, air traffic control systems, or weapons systems.